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(54) Title: POLISHING SLURRY COMPOSITION FOR IMPROVING SURFACE QUALITY OF SILICON WAFER AND METHOD FOR POLISHING SILICON WAFER USING THE SAME

(57) Abstract: Disclosed herein is a slurry composition for polishing a silicon wafer. The polishing slurry composition comprises deionized water, colloidal silica, a pH-adjusting agent and a water-soluble thickening agent, characterized in that the composition comprises at least one chelating agent selected from acetate chelating agents and phosphate chelating agents. The slurry composition exhibits markedly improved storage stability. Particularly, when the slurry composition is used for final polishing of a silicon wafer, the formation of haze, LPDs and surface microroughness on the surface of a wafer can be markedly reduced.

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